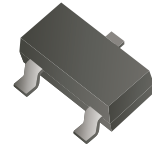


# CMS3407T-HF

**P-Channel**  
**RoHS Device**  
**Halogen Free**



V(BR)DSS	RDS(on)MAX	ID
-30V	50mΩ @ -10V	-4.1A
	75mΩ @ -4.5V	

## Features

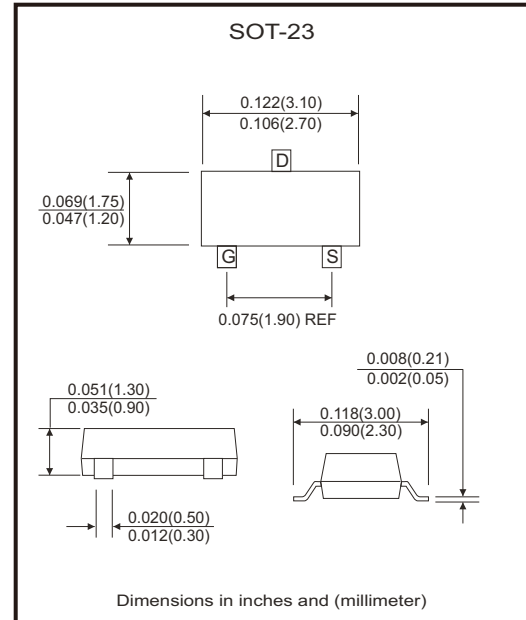
- Advanced high cell density trench technology.
- Low R<sub>DS(ON)</sub>
- Low gate charge.
- Green device available.

## Mechanical data

- Case: SOT-23, molded plastic.

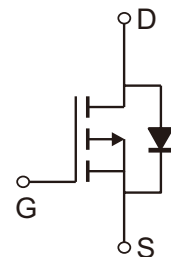
## Description

The CMS3407T is the highest performance trench P-ch MOSFETs with extreme high cell density, which provide excellent R<sub>DS(ON)</sub> and gate charge for use as a load switch or in PWM applications. The CMS3407T meet the RoHS and Green Product requirement with full function reliability approved.



## Circuit Diagram

- G : Gate
- S : Source
- D : Drain



## Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source voltage	V <sub>DS</sub>	-30	V
Gate-Source voltage	V <sub>GS</sub>	±20	V
Continuous drain current <sup>3</sup>	I <sub>D</sub> @ T <sub>A</sub> =25°C	-4.1	A
	I <sub>D</sub> @ T <sub>A</sub> =70°C	-3.5	A
Pulsed drain current <sup>1,2</sup>	I <sub>DM</sub> @ T <sub>A</sub> =25°C	-12	A
Total power dissipation	P <sub>D</sub> @ T <sub>A</sub> =25°C	1.38	W
Linear derating factor	-	0.01	W/°C
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>STG</sub>	-55 ~ +150	°C

## Thermal Data

Parameter	Symbol	Max. Value	Unit
Thermal resistance junction-ambient <sup>3</sup>	R <sub>θJA</sub>	90	°C/W

## Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Drain-Source breakdown voltage	$BV_{DSS}$	-30			V	$V_{GS}=0, I_D=-250\mu\text{A}$
Gate threshold voltage	$V_{GS(th)}$	-1.0		-3.0	V	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$
Forward transconductance	$g_{fs}$		8.2		S	$V_{DS}=-5\text{V}, I_D=-4\text{A}$
Gate-Source leakage current	$I_{GSS}$			$\pm 100$	nA	$V_{GS}=\pm 20\text{V}$
Drain-Source leakage current ( $T_J=25^\circ\text{C}$ )	$I_{DSS}$			-1	$\mu\text{A}$	$V_{DS}=-24\text{V}, V_{GS}=0$
Drain-Source leakage current ( $T_J=55^\circ\text{C}$ )				-5		$V_{DS}=-24\text{V}, V_{GS}=0$
Static drain-source on-resistance <sup>2</sup>	$R_{DS(on)}$			50	m $\Omega$	$V_{GS}=-10\text{V}, I_D=-4.1\text{A}$
				75		$V_{GS}=-4.5\text{V}, I_D=-3.0\text{A}$
Total gate charge <sup>2</sup>	$Q_g$		15.2		nC	$I_D=-3\text{A}$ $V_{DS}=-24\text{V}$ $V_{GS}=-10\text{V}$
Gate-Source charge	$Q_{gs}$		5.5			
Gate-Drain ("Miller") charge	$Q_{gd}$		1			
Turn-on delay time <sup>2</sup>	$T_{d(on)}$		8.6		ns	$V_{DS}=-15\text{V}$ $I_D=-1\text{A}$ $V_{GS}=-10\text{V}$ $R_G=6\Omega$ $R_D=15\Omega$
Rise time	$T_r$		12.2			
Turn-off delay time	$T_{d(off)}$		36.6			
Fall time	$T_f$		20.8			
Input capacitance	$C_{iss}$		590		pF	$V_{GS}=0\text{V}$ $V_{DS}=-25\text{V}$ $f=1.0\text{MHz}$
Output capacitance	$C_{oss}$		75			
Reverse transfer capacitance	$C_{rss}$		10			

## Source-Drain Diode

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Diode forward voltage <sup>2</sup>	$V_{SD}$			-1.2	V	$I_S=-1.0\text{A}, V_{GS}=0\text{V}, T_J=25^\circ\text{C}$
Continuous source current	$I_S$			-4.1	A	$V_G=V_D=0\text{V}$ , Force Current

- Notes: 1. Pulse width limited by Max. junction temperature.  
 2. Pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$ .  
 3. Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board; 270°C/W when mounted on min. copper pad.

## Rating and Characteristic Curves

### TYPICAL CHARACTERISTIC

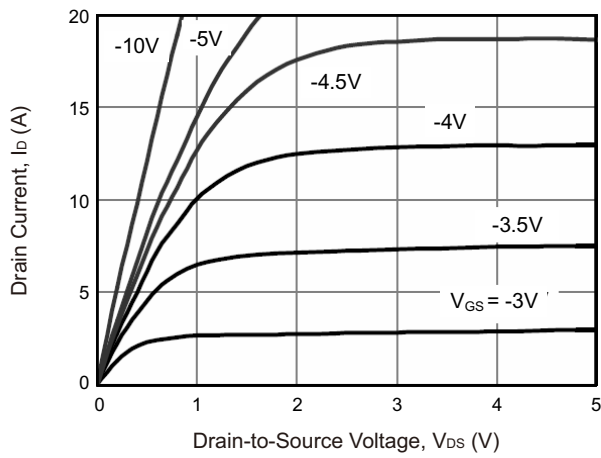


Fig.1 - Typical Output Characteristics

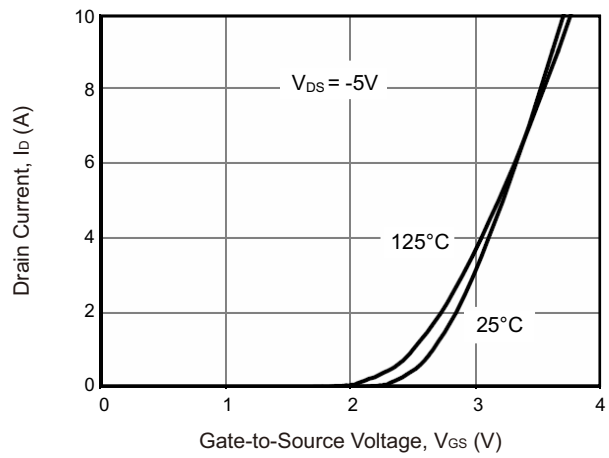


Fig.2 - Transfer Characteristics

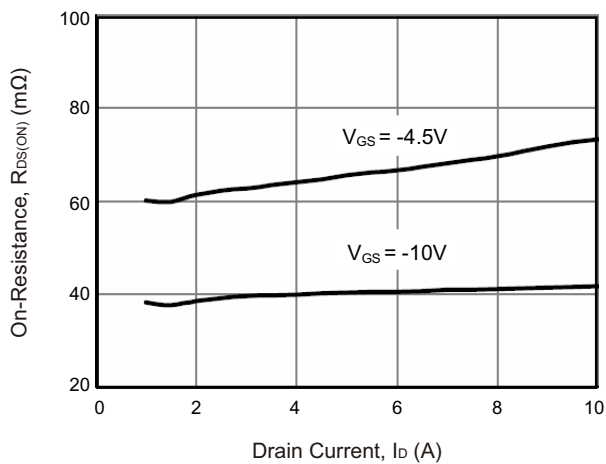


Fig.3 - On-Resistance vs. Drain Current

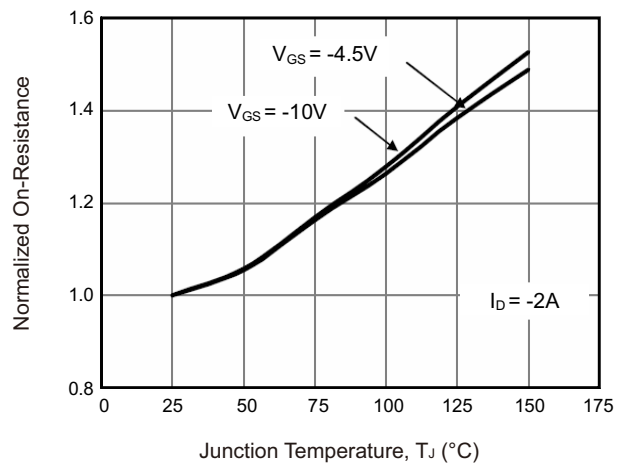


Fig.4 - Normalized  $R_{DS(ON)}$  vs.  $T_J$

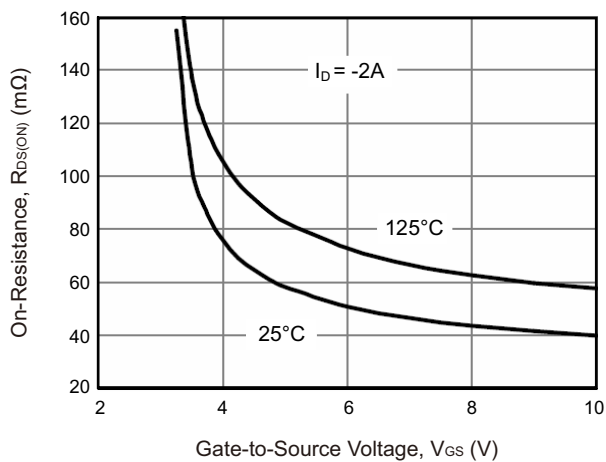


Fig.5 - On-Resistance vs. G-S Voltage

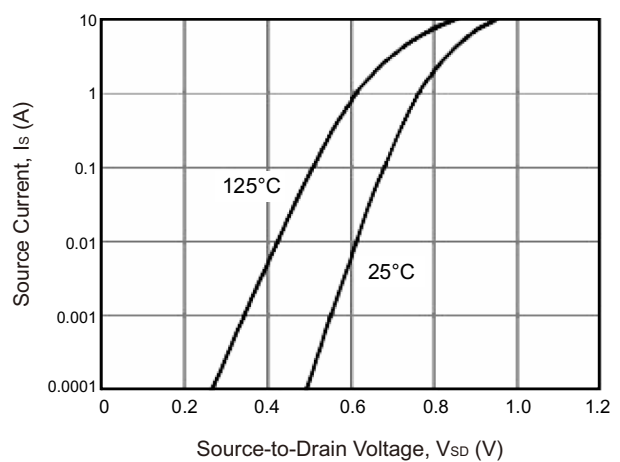


Fig.6 - Forward Characteristics of Reverse

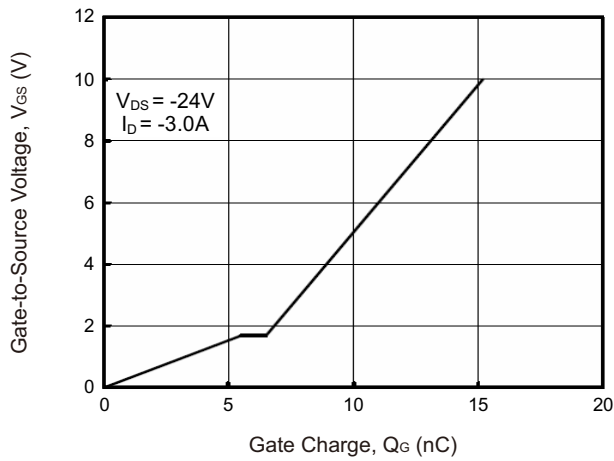


Fig.7 - Gate Charge Characteristics

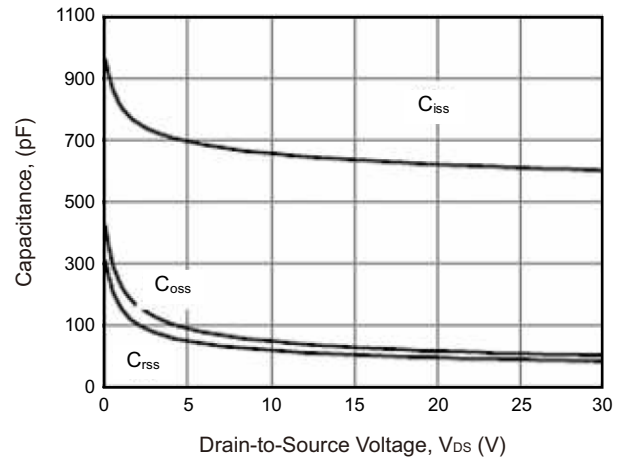


Fig.8 - Capacitance Characteristics

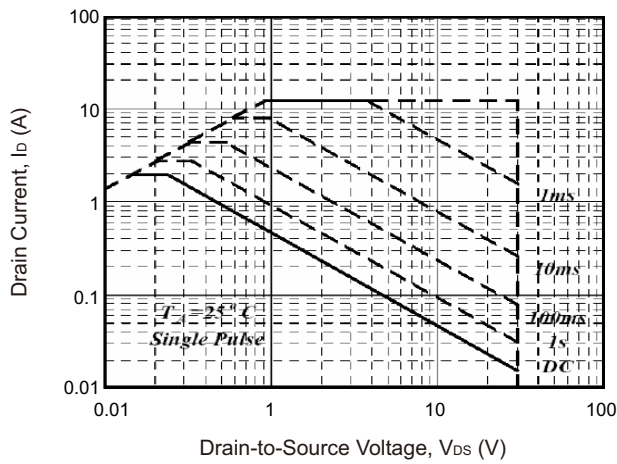


Fig.9 - Safe Operating Area

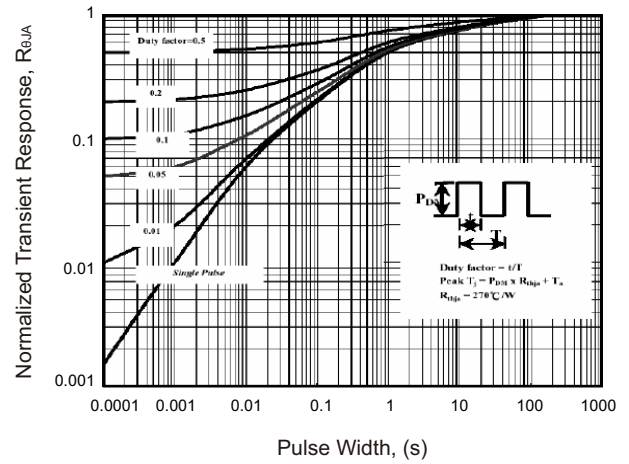


Fig.10 - Transient Thermal Impedance

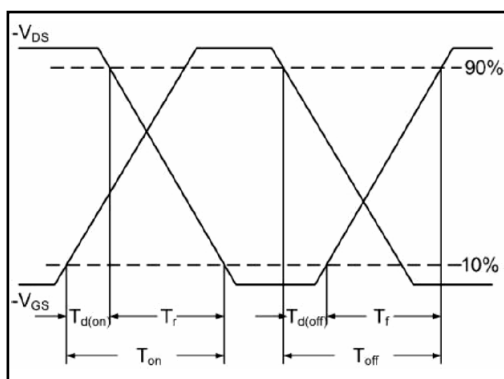


Fig.11 - Switching Time Waveform

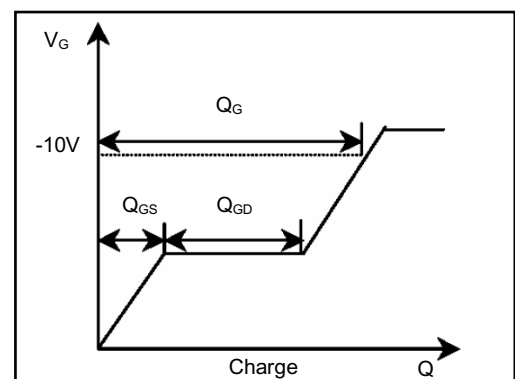
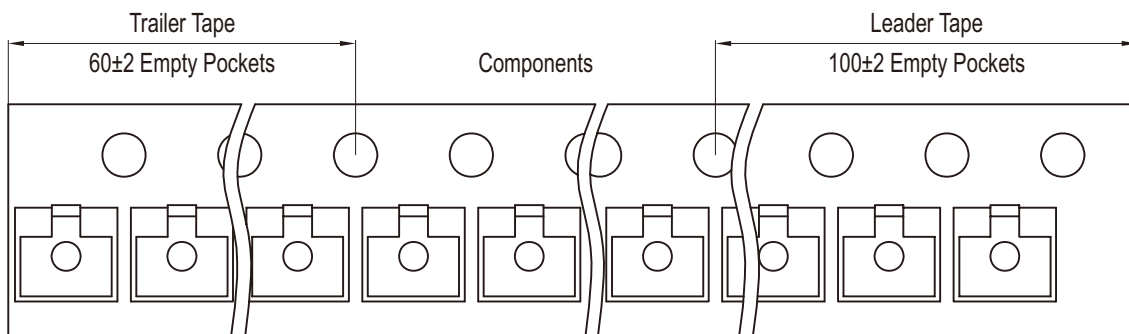
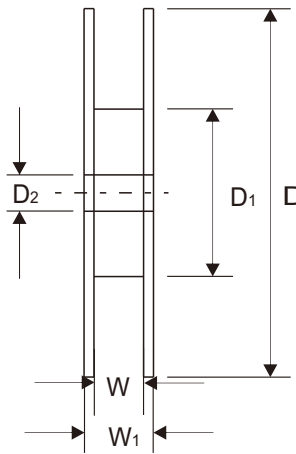
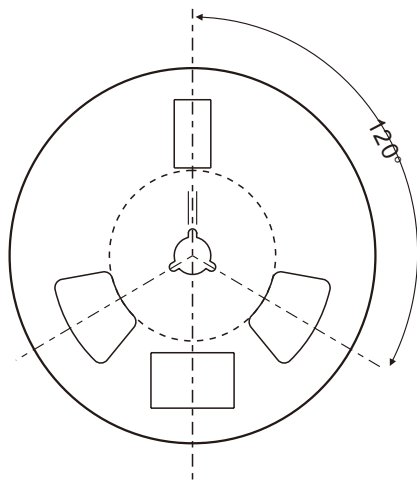
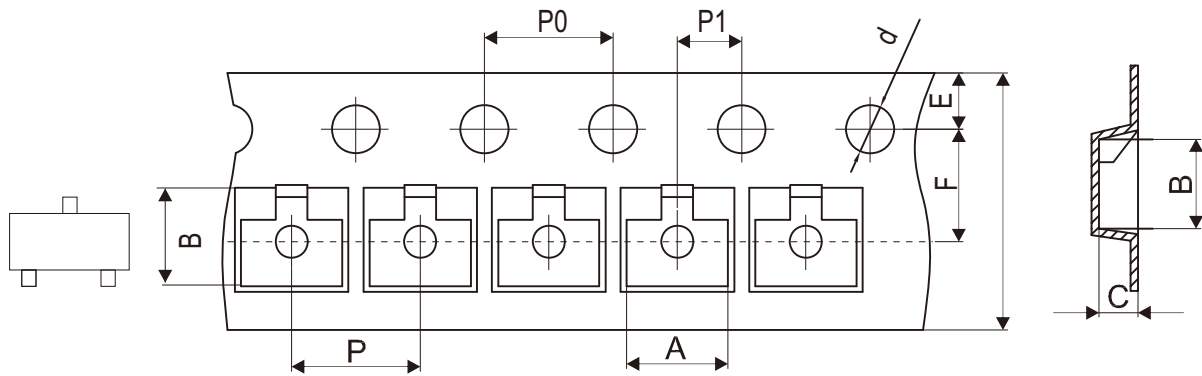


Fig.12 - Gate Charge Waveform

## Reel Taping Specification

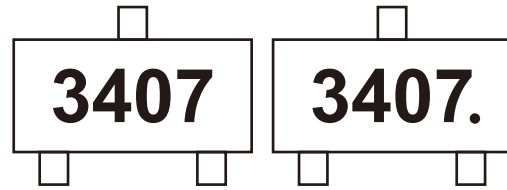


SOT-23	SYMBOL	A	B	C	d	D	D1	D2
	(mm)	3.10 ± 0.10	3.20 ± 0.10	1.37 ± 0.10	1.50 ± 0.10	178.00 ± 2.00	54.40 ± 1.00	13.00 ± 1.00
	(inch)	0.122 ± 0.004	0.126 ± 0.004	0.054 ± 0.004	0.059 ± 0.004	7.008 ± 0.079	2.142 ± 0.039	0.512 ± 0.039

SOT-23	SYMBOL	E	F	P	P0	P1	W	W1
	(mm)	1.75 ± 0.10	3.50 ± 0.10	4.00 ± 0.10	4.00 ± 0.10	2.00 ± 0.10	8.40 + 1.50 / - 0.50	12.00 ± 1.50
	(inch)	0.069 ± 0.004	0.138 ± 0.004	0.157 ± 0.004	0.157 ± 0.004	0.079 ± 0.004	0.330 + 0.012 / - 0.004	0.472 ± 0.039

## Marking Code

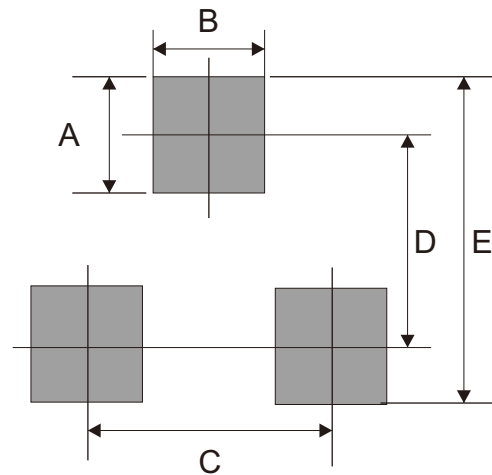
Part Number	Marking Code
CMS3407T-HF	3407



Solid dot = Control code

## Suggested P.C.B. PAD Layout

SIZE	SOT-23	
	(mm)	(inch)
A	0.80	0.031
B	0.60	0.024
C	2.20	0.087
D	2.37	0.093
E	2.97	0.117



## Standard Packaging

Case Type	REEL PACK	
	REEL (pcs)	Reel Size (inch)
SOT-23	3,000	7